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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

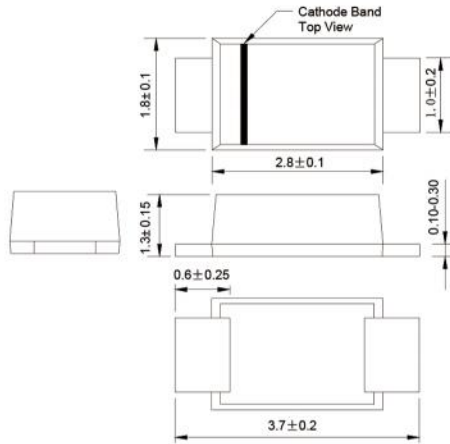
K110-TD

產品規格說明書

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 1.0 Ampere

SOD-123FL



Dimensions in millimeters

FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body

Terminals: Solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.0007 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

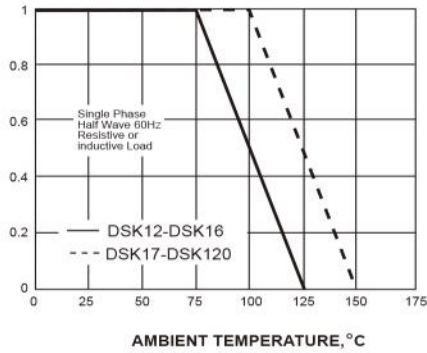
MDD Catalog Number	SYMBOLS	DSK12 K12	DSK13 K13	DSK14 K14	DSK15 K15	DSK16 K16	DSK17 K17	DSK18 K18	DSK19 K19	DSK110 K110	DSK115 K115	DSK120 K120	UNITS	
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	70	80	90	100	150	200	VOLTS	
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	49	56	63	70	105	140	VOLTS	
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	70	80	90	100	150	200	VOLTS	
Maximum average forward rectified current	I _(AV)	1.0											Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	25.0											Amps	
Maximum instantaneous forward voltage at 1.0A	V _F	0.55			0.70			0.85					0.95	Volts
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	0.5								0.2		mA		
		10.0				5.0				2.0				
Typical junction capacitance (NOTE 1)	C _J	110				80								pF
Operating junction temperature range	T _J	-65 to +125						-65 to +150						°C
Storage temperature range	T _{STG}	-65 to +150											°C	

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES K110

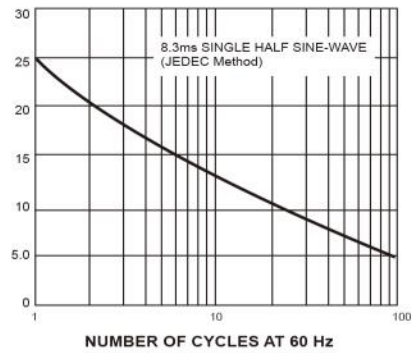
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



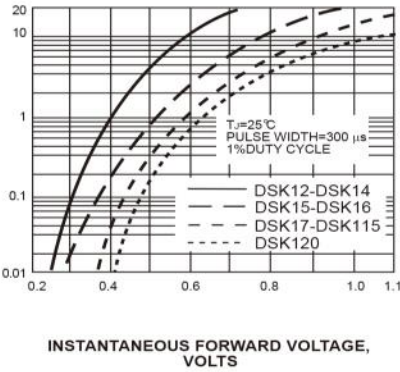
PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



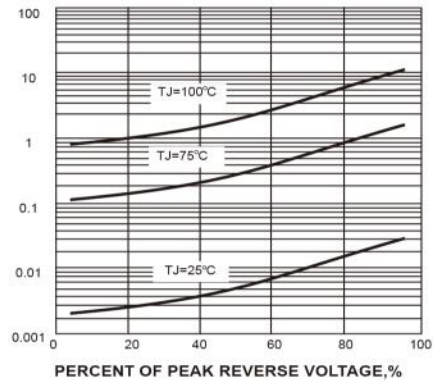
INSTANTANEOUS FORWARD
CURRENT, AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



INSTANTANEOUS REVERSE CURRENT,
MILLIAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE

